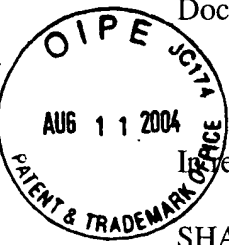


1F12 2823

Docket No.: 005920 USA/PMG/PCTRL

PATENT/OFFICIAL



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

SHANMUGASUNDRAM et al.

Serial No. 09/943,383

Filed: August 31, 2001

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Group Art Unit: 2823

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Examiner: William D. Coleman

For: IN SITU SENSOR BASED CONTROL OF SEMICONDUCTOR PROCESSING
PROCEDURE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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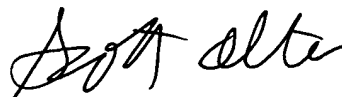
to present to the Office the relevant facts and law regarding the appropriate status of such document.

The references listed on Sheet 1 of the attached PTO-1449 Forms were cited in a patentability investigation and/or a corresponding foreign or PCT application relating to the above-referenced application. The remaining references are from potentially related patent applications, and possibly other sources.

Please charge the fee of \$180.00 under 37 CFR 1.17(p) to Deposit Account No. 08-0219. The Commissioner is hereby authorized to charge any additional fees that may be required for this submission, or credit any overpayment to deposit account no. 08-0219.

Respectfully submitted,

Wilmer Cutler Pickering Hale and Dorr LLP



Scott M. Alter

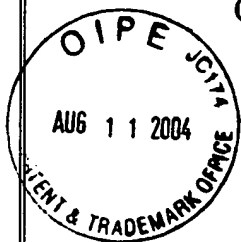
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